



10N40

Preliminary

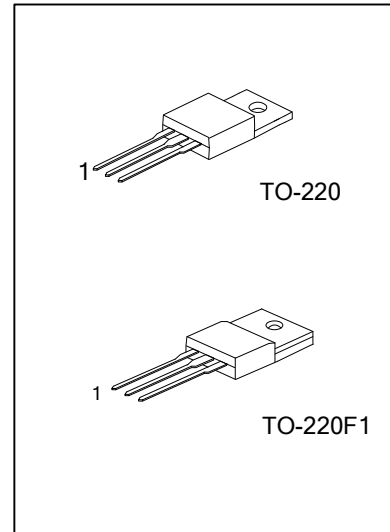
Power MOSFET

10.5A, 400V N-CHANNEL POWER MOSFET

DESCRIPTION

The UTC **10N40** is an N-channel mode power MOSFET using UTC's advanced technology to provide customers with planar stripe and DMOS technology. This technology specializes in allowing a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

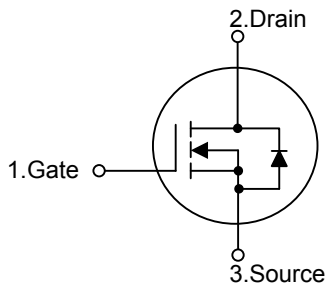
The UTC **10N40** is universally applied in electronic lamp ballast based on half bridge topology and high efficient switched mode power supply.



FEATURES

- * High switching speed
- * $R_{DS(ON)}=0.65\Omega @ V_{GS}=10V$
- * 100% avalanche tested

SYMBOL



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
10N40L-TA3-T	10N40G-TA3-T	TO-220	G	D	S	Tube
10N40L-TF1-T	10N40G-TF1-T	TO-220F1	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>10N40L-TA3-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Lead Free</p>	<p>(1) T: Tube</p> <p>(2) TA3: TO-220, TF1: TO-220F1</p> <p>(3) G: Halogen Free, L: Lead Free</p>
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■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	400	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous ($T_C=25^\circ\text{C}$)	I_D	10.5	A
	Pulsed (Note 2)	I_{DM}	42	A
Avalanche Current (Note 2)		I_{AR}	11	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	360	mJ
	Repetitive (Note 4)	E_{AR}	13.5	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220	P_D	135	W
	TO-220F1		44	W
Derate above 25°C	TO-220		1.07	W/ $^\circ\text{C}$
	TO-220F1		0.35	W/ $^\circ\text{C}$
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55~+150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature

3. $L = 5.7\text{mH}$, $I_{AS} = 10.5\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 10.5\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient		θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220	θ_{JC}	0.93	$^\circ\text{C}/\text{W}$
	TO-220F1		2.86	

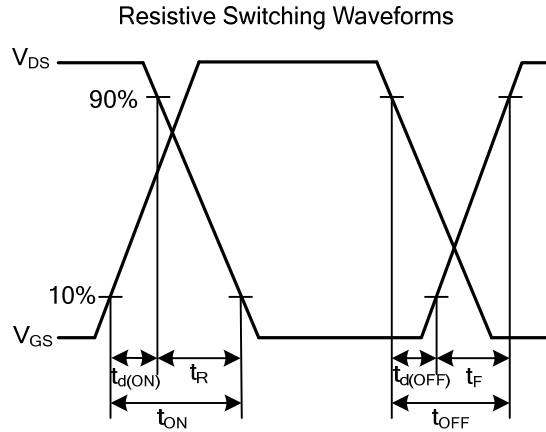
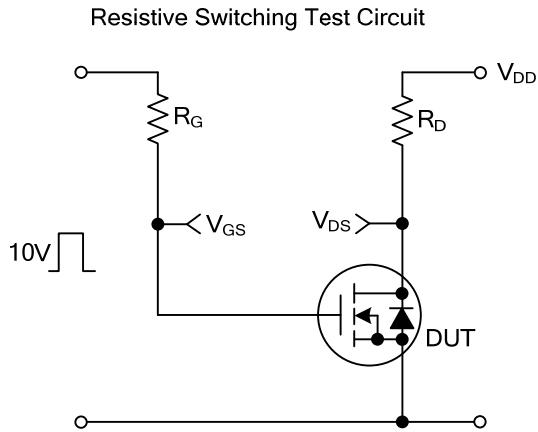
■ ELECTRICAL CHARACTERISTICS (T_c=25°C, unless otherwise noted)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	I _D =250μA, V _{GS} =0V	400			V
Breakdown Voltage Temperature Coefficient		ΔBV _{DSS} /ΔT _J	Reference to 25°C, I _D =250μA		0.54		V/°C
Drain-Source Leakage Current		I _{DSS}	V _{DS} =400V, V _{GS} =0V			1	μA
Gate- Source Leakage Current	Forward	I _{GSS}	V _{GS} =+30V, V _{DS} =0V			+100	nA
	Reverse		V _{GS} =-30V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =5.25A		0.5	0.65	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		840	1090	pF
Output Capacitance		C _{OSS}			250	325	pF
Reverse Transfer Capacitance		C _{RSS}			80	110	pF
SWITCHING PARAMETERS							
Total Gate Charge		Q _G	V _{GS} =10V, V _{DS} =320V, I _D =10.5A (Note 1, 2)		28	35	nC
Gate to Source Charge		Q _{GS}			4		nC
Gate to Drain Charge		Q _{GD}			15		nC
Turn-ON Delay Time		t _{D(ON)}	V _{DD} =200V, I _D =10.5A, R _G =25Ω (Note 1, 2)		14	40	ns
Rise Time		t _R			89	190	ns
Turn-OFF Delay Time		t _{D(OFF)}			81	170	ns
Fall-Time		t _F			81	170	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I _S				10.5	A
Maximum Body-Diode Pulsed Current		I _{SM}				42	A
Drain-Source Diode Forward Voltage		V _{SD}	I _S =10.5A, V _{GS} =0V			1.4	V
Body Diode Reverse Recovery Time		t _{rr}	I _S =10.5A, V _{GS} =0V,		290		ns
Body Diode Reverse Recovery Charge		Q _{RR}	dI _F /dt=100A/μs (Note 1)		2.4		μC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%

2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS



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